Gate

Poly

Exercise 1

1-1. Two layouts of n-channel MOSFET are shown in Fig.1.1. What is the width and length of the two devices?

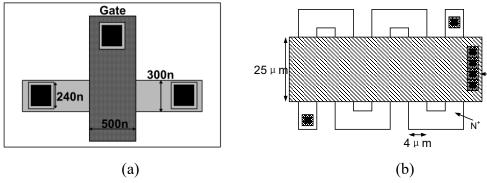
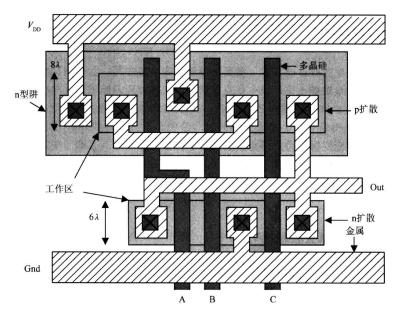


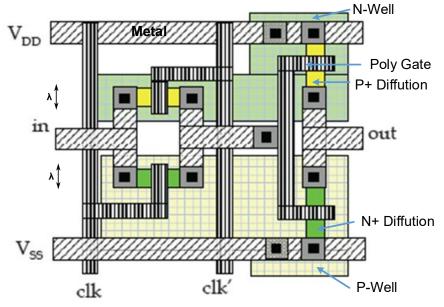
Fig.1.1

Answer:

- (a) Length=500n; Width=300n
- (b) Length= $5 \times 25 \mu m = 125 \mu m$; Width= $4 \mu m$
- 1-2. The layouts of a circuit are shown in Fig.1.2. Give the corresponding schematics and its function, and mark the W/L sizes of each transistor. Assume $L=2\lambda$, $\lambda=0.4\mu m$.



(a) p-sub, n-well technology

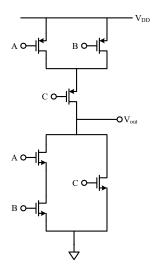


(b) dual-well technology, and $clk' = \overline{clk}$

Fig.1.2

Answer:

(a)



Out=
$$\overline{AB+C}$$

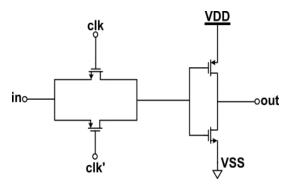
W/L of N-MOSFET:

$$\frac{6\lambda}{2\lambda} = \frac{6 \times 0.4}{2 \times 0.4} = \frac{2.4}{0.8}$$

W/L of P-MOSFET:

$$\frac{8\lambda}{2\lambda} = \frac{8 \times 0.4}{2 \times 0.4} = \frac{3.2}{0.8}$$

(b)



CLK high: Out= \overline{IN} CLK low: Out=0

W/L of N-MOSFET:

$$\frac{\lambda}{2\lambda} = \frac{0.4}{2 \times 0.4} = \frac{0.4}{0.8}$$

W/L of P-MOSFET:

$$\frac{\lambda}{2\lambda} = \frac{0.4}{2 \times 0.4} = \frac{0.4}{0.8}$$

1-3. Layout of a different pair with PMOS current source loads in p-sub N-well technology is shown as Fig.1.3. Give the corresponding schematics and mark the W/L sizes of each transistor. Assume λ =0.4 μ m.

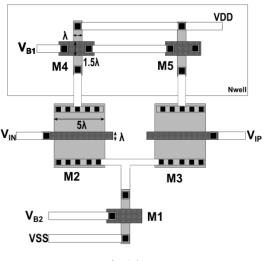


Fig.1.3

Answer:

